Abstracts

Design and characterization of FET based cold/hot noise sources

L.P. Dunleavy, M.C. Smith, S.M. Lardizabal, A. Fejzuli and R.S. Roeder. "Design and characterization of FET based cold/hot noise sources." 1997 MTT-S International Microwave Symposium Digest 3. (1997 Vol. III [MWSYM]): 1293-1296.

Innovative design, modeling, and characterization methods are described for FET cold noise sources. A developed InP HEMT cold/hot noise source demonstrates 105 K in the 18-22 GHz range; the highest reported frequency for a FET cold noise source. Measurements confirm variable source temperature from 105 K to over 1000 K.

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